

MN3005

4096-STAGE LONG DELAY BBD

■ General description

The MN3005 is a world's first 4096-stage long delay BBD, 8 times longer than 512-stage BBD manufactured by using a P-channel low noise silicon gate process.

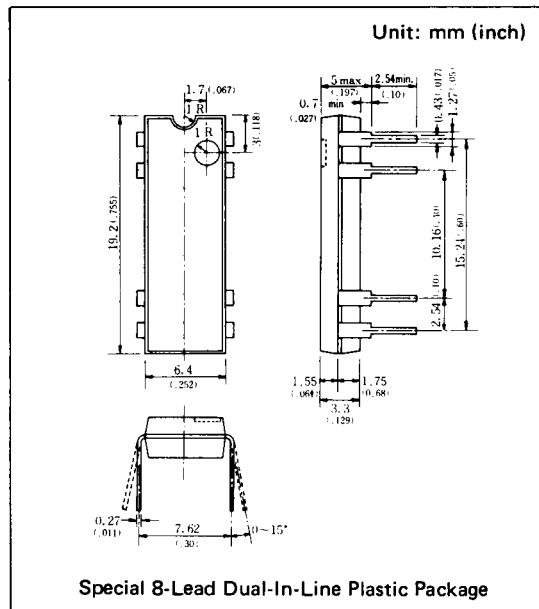
Long signal delay time 205ms can be obtained at clock frequency 10KHz. S/N is 75dB. S/N has been improved by more than 20dB in comparing with 8-connected 512-stage BBD's. The MN3005 is suitably used for reverberation and echo effects in electronic musical instruments such as electronic organ, guitar amplifier and music synthesizer which need long delay time.

■ Features

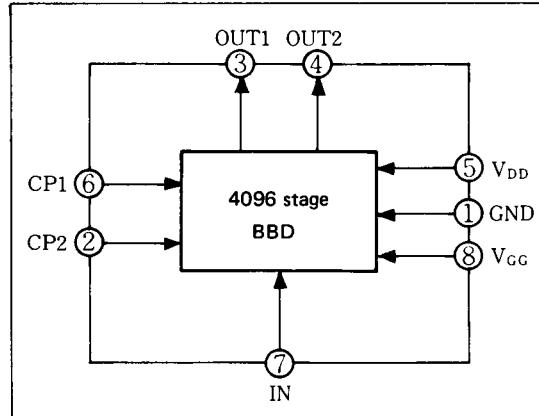
- 1 chip 4096 stage and wide range of variable delay times: 20.48 ~ 204.8ms.
- High S/N in spite of multi-stage and wide dynamic range: S/N \geq 75dB typ.
- No insertion loss since the loss occurring in the signal transfer is corrected by the MOS capacity of input and output. $L_i = 0$ dB.
- High integration and high reliability by using P channel low noise silicon gate process.
- Special 8 lead dual-in-line plastic package.

■ Applications

- Reverberation and echo effects in echo microphone and stereo equipment.
- Chorus effect in electronic musical instruments.
- Variable or fixed delay of analog signals.
- Telephone time compression and delay line for voice communication systems, etc.



■ Block Diagram



■ Quick Reference Data

Item	Symbol	Value	Unit
Supply Voltage	V _{DD} , V _{GG}	-15, V _{DD} +1	V
Signal Delay Time	t ₀	20.48~204.8	ms
Total Harmonic Distortion	THD	1	%
Signal to Noise Ratio	S/N	75	dB

■ Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Terminal Voltage	V _{DD} , V _{GG} , V _{CP} , V _I	-18~+0.3	V
Output Voltage	V _O	-18~+0.3	V
Operating Temperature	T _{OPR}	-20~+60	°C
Storage Temperature	T _{STG}	-55~+125	°C

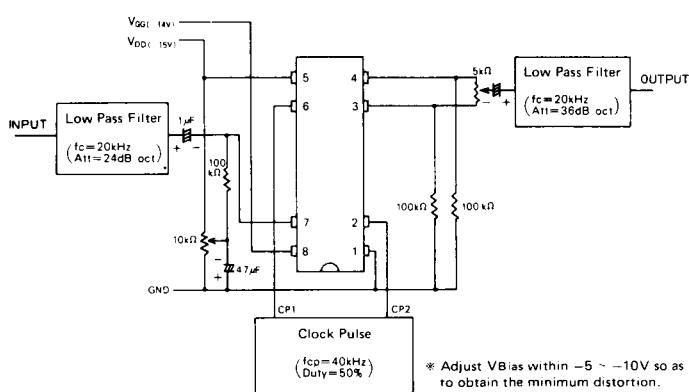
■ Operating Conditions (Ta = 25°C)

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain Supply Voltage	V _{DD}		-14	-15	-16	V
Gate Supply Voltage	V _{GG}			V _{DD} +1		V
Clock Voltage "H" Level	V _{CPL}		0		-1	V
Clock Voltage "L" Level	V _{CPH}			V _{DD}		V
Clock Input Capacitance	C _{CP}				2800	pF
Clock Frequency	f _{CP}		10		100	kHz
Clock Pulse Width *2	t _{CPW}	Test Circuit			0.5T*2	
Clock Rise Time *2	t _{CPR}	Test Circuit			500	ns
Clock Fall Time *2	t _{Cpf}	Test Circuit			500	ns
Clock Cross Point	V _X		0		-3	V
Input DC Bias Voltage	V _{Bias}		-5		-10	V

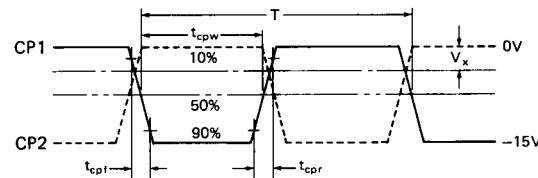
■ Electrical Characteristics (Ta = 25°C, V_{DD} = V_{CPL} = -15V, V_{CPH} = 0V, V_{GG} = -14V, R_L = 100kΩ)

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Signal Delay Time	t _D		20.48		204.8	ms
Input Signal Frequency	f _i	f _{CP} =40kHz, V _i =1.0Vrms, Output Attenuation ≤ 3dB (0dB at f _i =1kHz)	10			kHz
Input Signal Swing	V _i	f _{CP} =40kHz, f _i =1kHz, THD=2.5%	1.0			Vrms
Insertion Loss	L _i	f _{CP} =40kHz, f _i =1kHz, V _i =1.0Vrms	-4	0	4	dB
Total Harmonic Distortion	THD	f _{CP} =40kHz, f _i =1kHz, V _i =0.78Vrms		1	2.5	%
Noise Voltage	V _{no}	f _{CP} =100kHz Weighted by "A" curve			0.4	mVrms
Signal to Noise Ratio	S/N			75		dB

■ Test Circuit

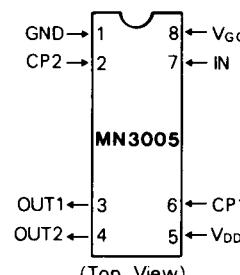


*1 Clock Pulse Waveforms

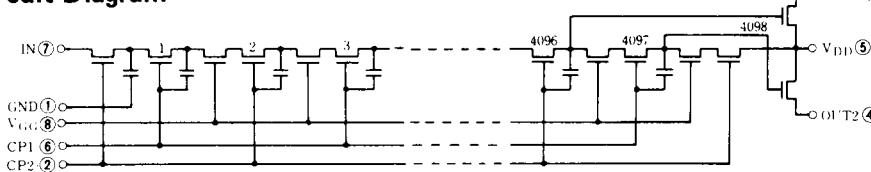


*2 T = 1/f_{CP}

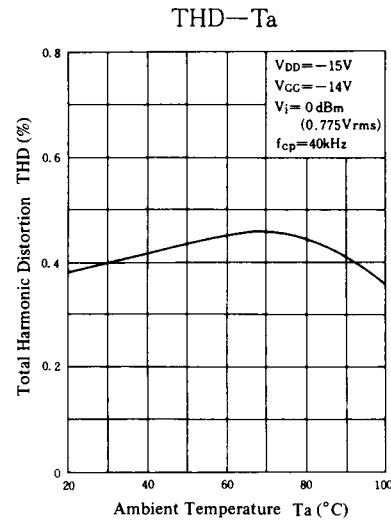
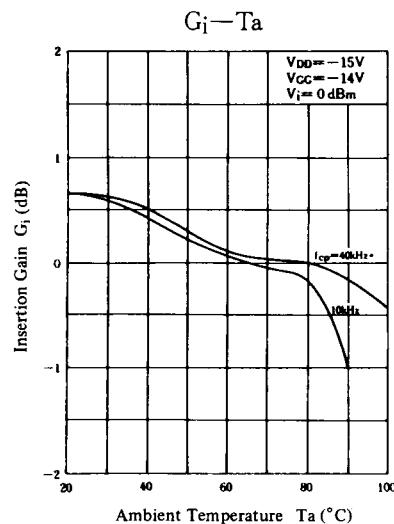
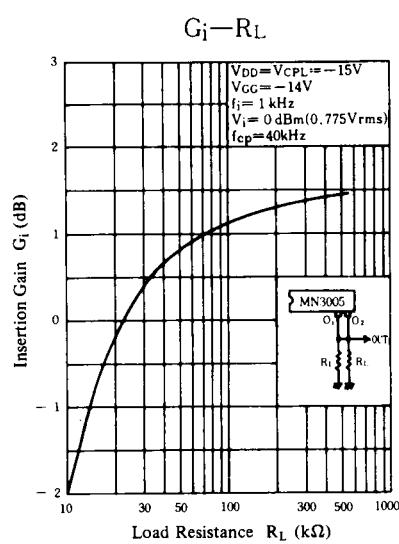
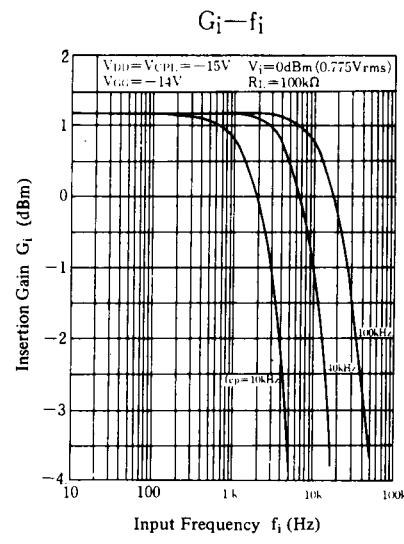
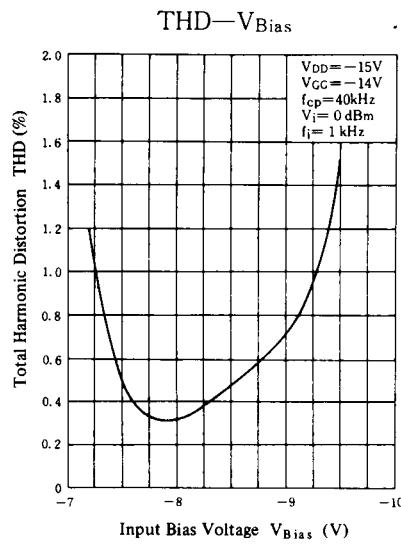
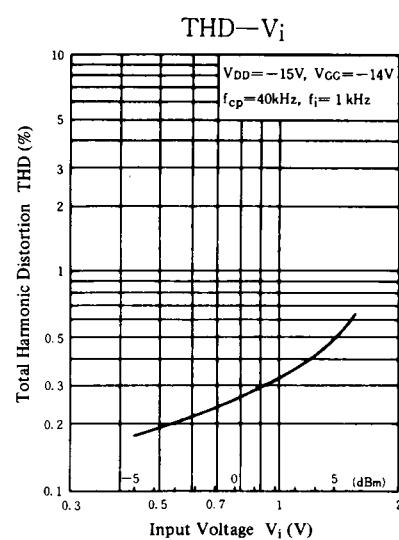
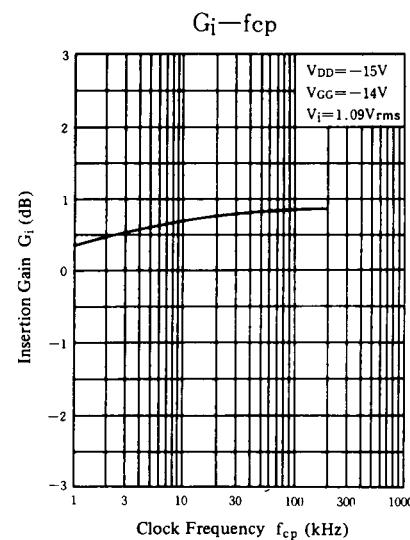
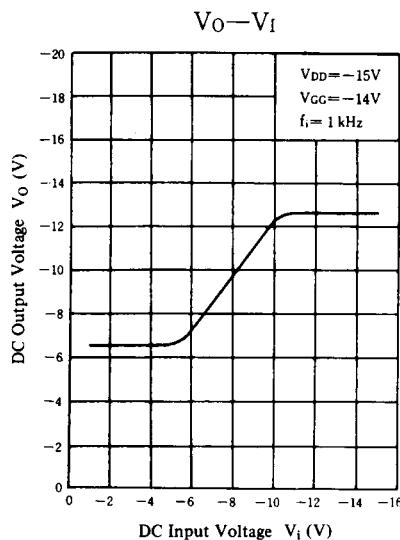
■ Terminal Assignments



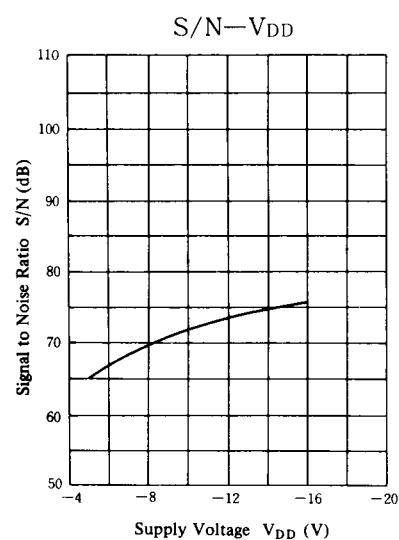
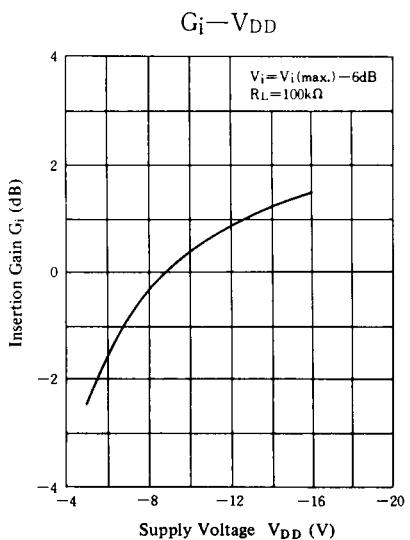
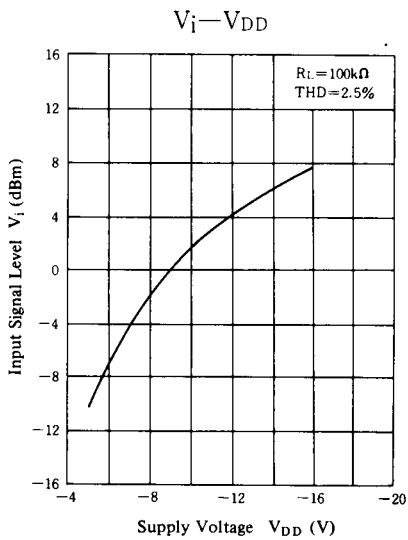
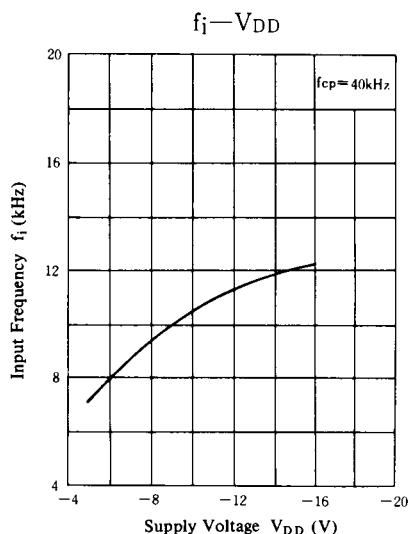
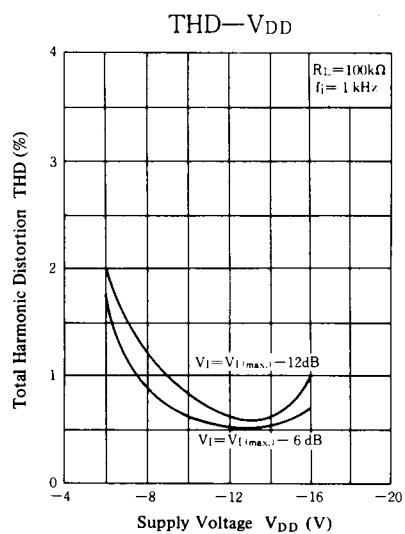
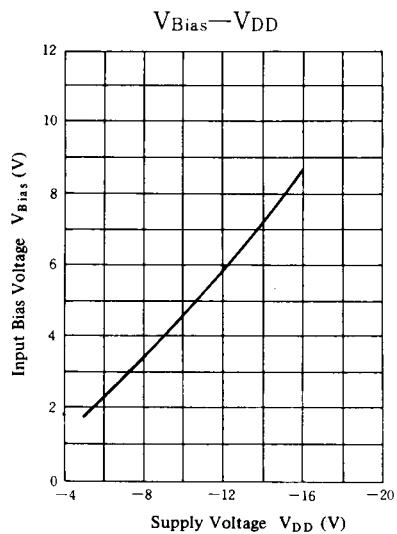
■ Circuit Diagram



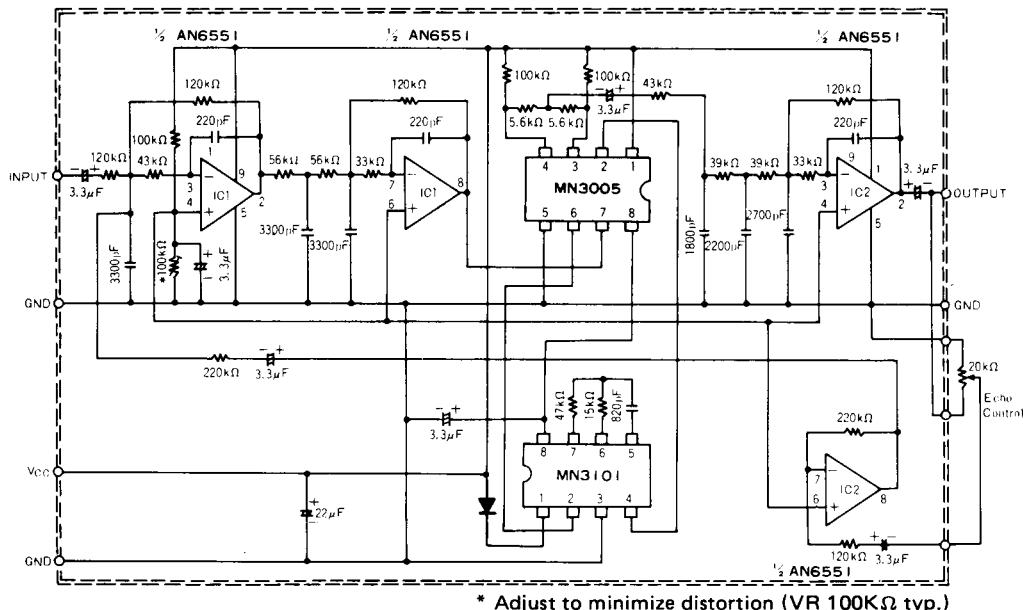
■ Typical Electrical Characteristic Curves



■ Supply Voltage Characteristics



■ Application Circuit



* Adjust to minimize distortion (VR 100KΩ typ.)

Reverberation Effect Generation Circuit (Signal Delay Over 100msec.)

■ Pattern Drawing of the Printed Circuit Board (Real size)

